



## PRESS - PACK RECTIFIER DIODE D243-630

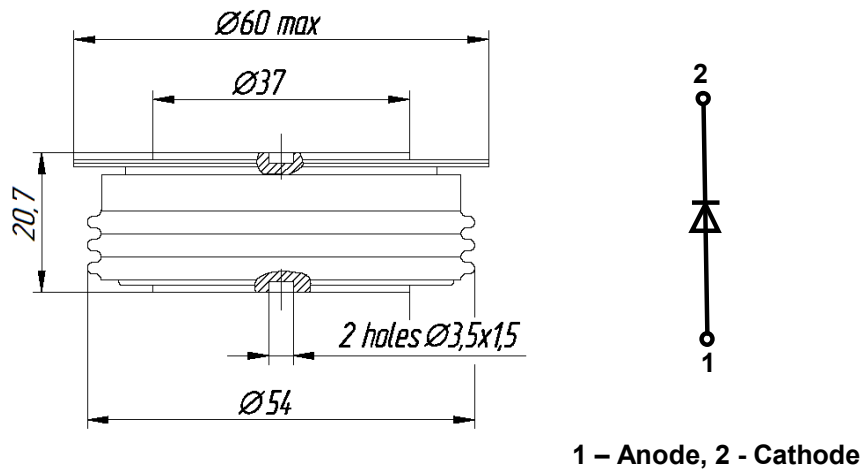
<ul style="list-style-type: none"> <li>◆ <math>V_{RRM} = \underline{5200-6000\text{ V}}</math></li> <li>◆ <math>I_{F(AV)} = \underline{840\text{ A}}</math> (<math>T_C = 85^\circ\text{C}</math>)</li> <li>◆ <math>I_{FSM} = \underline{8,0\text{ kA}}</math> (<math>t_p=10\text{ms}</math>)</li> </ul>			
<ul style="list-style-type: none"> <li>◆ Low forward losses</li> <li>◆ Low dispersion <math>Q_{RR}</math> and <math>V_{FM}</math> for series and parallel connections</li> <li>◆ Press-pack design</li> </ul>			
<b>MAXIMUM RATED VALUES</b>			
Parameter and conditions	Symbol	Values	Units
Repetitive peak reverse voltage, $T_j = -60 \dots +150\text{ }^\circ\text{C}$	$V_{RRM}$	5200-6000	V
Non- repetitive peak reverse voltage, $T_j = -60 \dots +150\text{ }^\circ\text{C}$	$V_{RSM}$	5300-6100	
Repetitive peak reverse current, $T_j = 150\text{ }^\circ\text{C}$ , $V_R = V_{RRM}$	$I_{RRM}$	70	mA
Maximum average forward current, $T_C = 85\text{ }^\circ\text{C}$ , $f = 50\text{ Hz}$	$I_{F(AV)}$	840	A
RMS forward current, $T_C = 85\text{ }^\circ\text{C}$ , $f = 50\text{ Hz}$	$I_{FRMS}$	1310	
Surge non-repetitive current, $T_j = 150\text{ }^\circ\text{C}$ , $V_R = 0$ , $t_p = 10\text{ ms}$	$I_{FSM}$	8,0	kA
Safety factor	$I^2t$	$320 \cdot 10^3$	$\text{A}^2\text{s}$
Operation junction temperature range	$T_j$	-60 ... +150	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-60 ... +50	

**D243-630**

<b>ELECTRICAL CHARACTERISTICS</b>					
Parameter and conditions	Symbol	Values			Units
		min	typ.	max	
Maximum peak forward voltage, $T_j = 25\text{ °C}$ , $I_F = 1980\text{ A}$	$V_{FM}$	-	-	2,50	V
On-state threshold voltage, $T_j = 150\text{ °C}$ , $I_F = 990 - 2970\text{ A}$	$V_{(TO)}$	-	-	0,90	
On-state slope resistance, $T_j = 150\text{ °C}$ , $I_F = 990 - 2970\text{ A}$	$r_T$	-	-	0,90	mΩ
Recovery charge, $T_j = 150\text{ °C}$ , $I_F = 630\text{ A}$ , $di_F/dt = -5\text{ A}/\mu\text{s}$ , $V_R \geq 100\text{ V}$	$Q_{RR}$	-	-		μAs
Recovery current, $T_j = 150\text{ °C}$ , $I_F = 630\text{ A}$ , $di_F/dt = -5\text{ A}/\mu\text{s}$ , $V_R \geq 100\text{ V}$	$I_{RR}$	-	-		A
<b>THERMAL PARAMETERS</b>					
Thermal resistance junction to case, DC per diode double side cooled anode side cooled cathode side cooled	$R_{th(j-c)}$	-	-	0,027 0,054 0,054	°C/W
Thermal resistance case to heatsink, double side cooled single side cooled	$R_{th(c-h)}$	-	-	0,01 0,02	
<b>MECHANICAL PARAMETERS</b>					
Weight	w	-	0,24	-	kg
Mounting force	F	13,5		16,5	kN
Maximum acceleration (at nominal mounting force)	a	-	-	100	m/s <sup>2</sup>



**D243-630**



**Fig. 1. Device Outline Drawing**  
(dimensions in mm)



126, Proletarskaya str.,  
430001, Saransk, Republic Mordovia, Russia  
Tel: +7(8342) 47-04-30  
Tel/Fax: +7 (8342) 47-15-01  
E-mail: vpruvs@elvpr.ru  
Internet: www.elvpr.ru